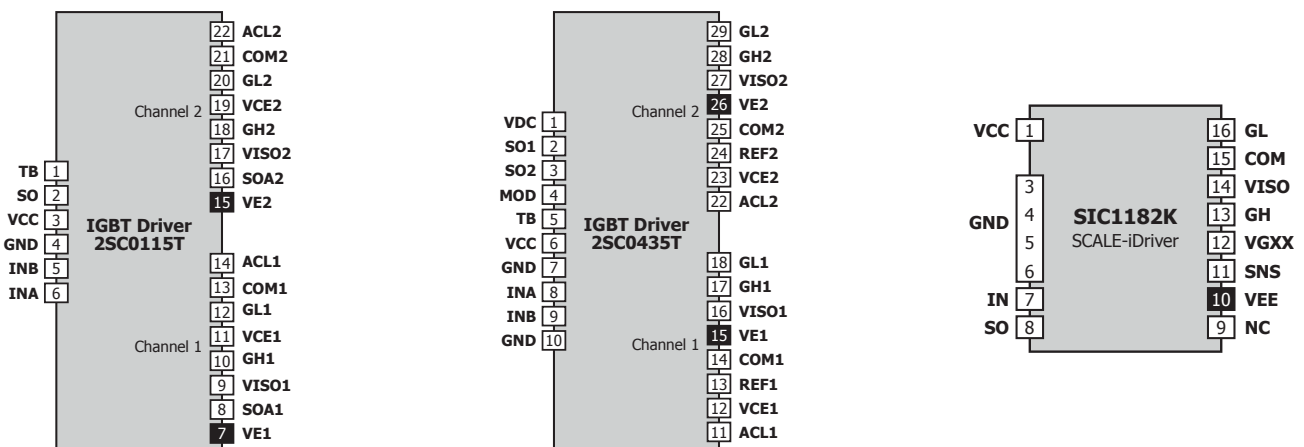
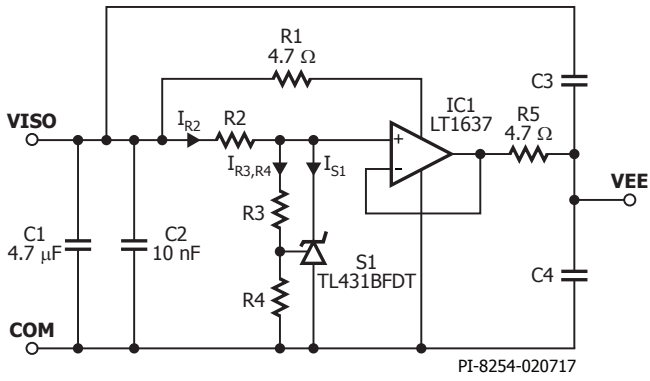


# SiC MOSFET Gate Driver Cores 600 V – 3300 V

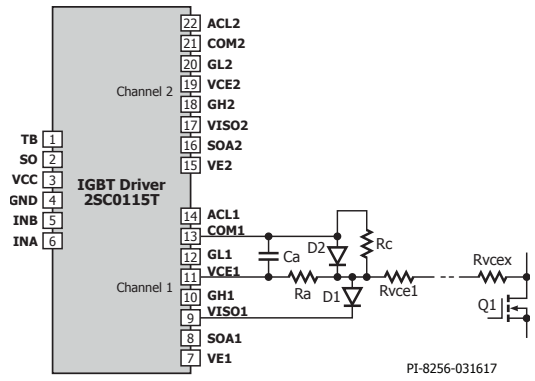
- Variable gate voltage by VEE circuit (0 V – 25 V, 0 V – 10 V)
- $\leq 2 \mu\text{s}$  short-circuit response time
- High output current and isolation capabilities
- High switching frequency up to 500 kHz
- SiC MOSFET breakdown voltage up to 3.3 kV
- Suitable for all SiC MOSFET designs

## Pinning of SCALE™ Gate Driver Cores (2SC0115T, 2SC0435T) SCALE-iDriver™ IC (SIC1182K) with Marked VEx / VEE Pins





VEE regulator for SiC MOSFET switches with regulated positive rail



Modified setting for SiC MOSFET short-circuit detection

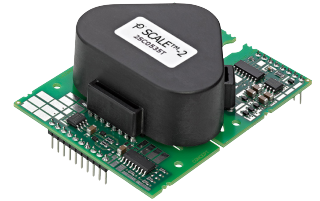
## Gate Driver Cores



2SC0115T2A0-12



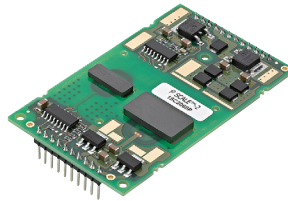
2SC0650P2x0-17



2SC0535T2xx-33



2SC0435T2xx-17



1SC2060P2A0-17

## Design Support

### Application Note

Controlling SiC MOSFET power switches with SCALE-2 and SCALE-2+ gate driver cores (AN-1601) ([www.power.com/an-1601](http://www.power.com/an-1601))

### Reference Designs

Gate driver reference designs ([www.power.com/solutions/designs/gate-drivers](http://www.power.com/solutions/designs/gate-drivers))